**Product data sheet** 

# 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers

### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and logic ICs
- · High commutation capability
- High voltage capability
- · Planar passivated for voltage ruggedness and reliability
- · Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

## 3. Applications

- Electronic thermostats
- General purpose motor controls

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}C$ ; $\overline{Fig. 1}$ ; Fig. 2; Fig. 3	-	-	8	Α
I <sub>TSM</sub> non-repetitive perstate current	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	-	65	Α
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	-	71	Α
Tj	junction temperature		-	-	125	°C
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	-	5	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	1.65	V
Dynamic char	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	20	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 0.1 V/µs; gate open circuit	6	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit; Fig. 12	2	-	-	A/ms

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2-D-T1
2	T2	main terminal 2		G sym051
3	G	gate		Symost
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
BTA208-600D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	8	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5	-	65	Α
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 16.7 ms	-	71	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	21	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 0.2 A	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

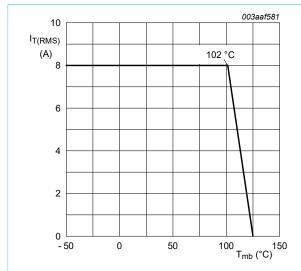


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

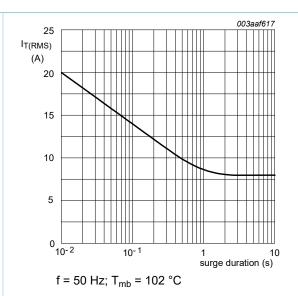


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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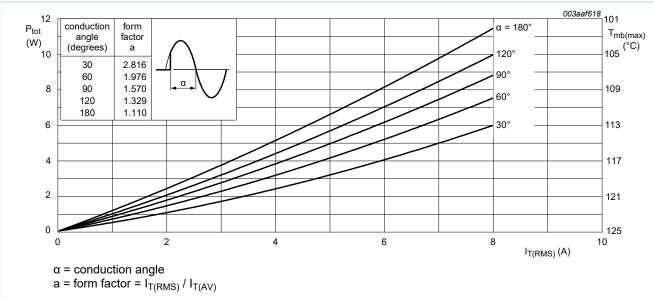


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

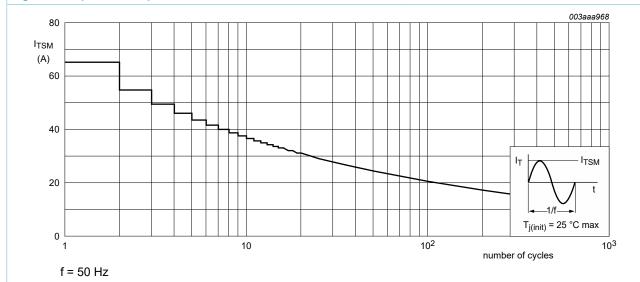
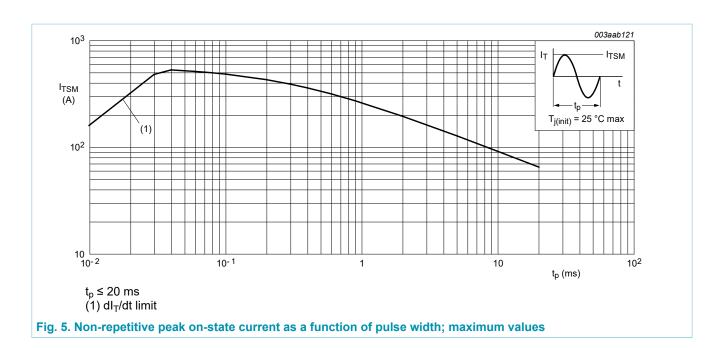


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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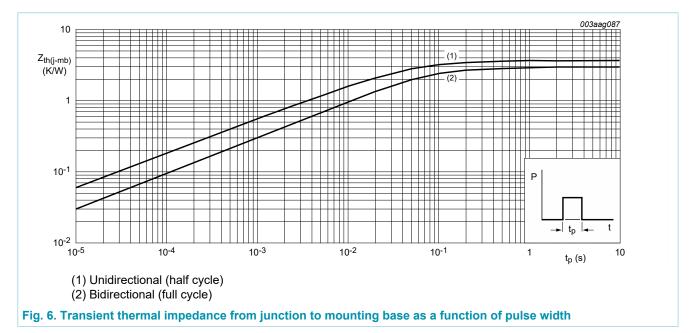
BTA208-600D

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub> thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W	
	_	half cycle; Fig. 6	_	-	2.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



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## 9. Characteristics

### Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;} $ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	5	mA
IL I	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	-	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	-	-	25	mA
l <sub>н</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic cl	haracteristics				,	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	20	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 0.1 V/µs; gate open circuit	6	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 8 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit; Fig. 12	2	-	-	A/ms

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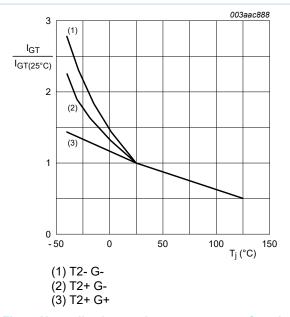


Fig. 7. Normalized gate trigger current as a function of junction temperature

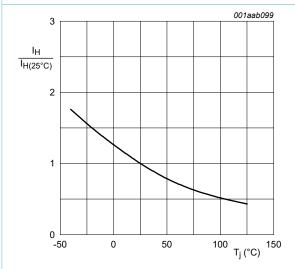


Fig. 9. Normalized holding current as a function of junction temperature

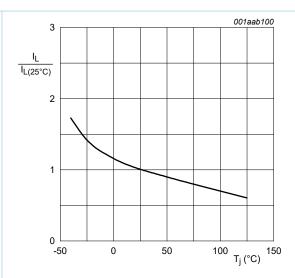
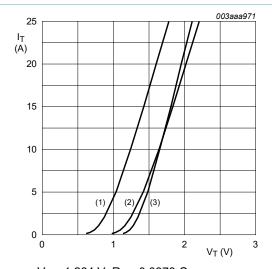


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.264 V;  $R_s$  = 0.0378  $\Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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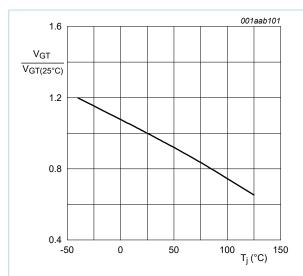


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

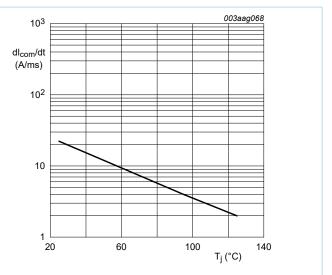
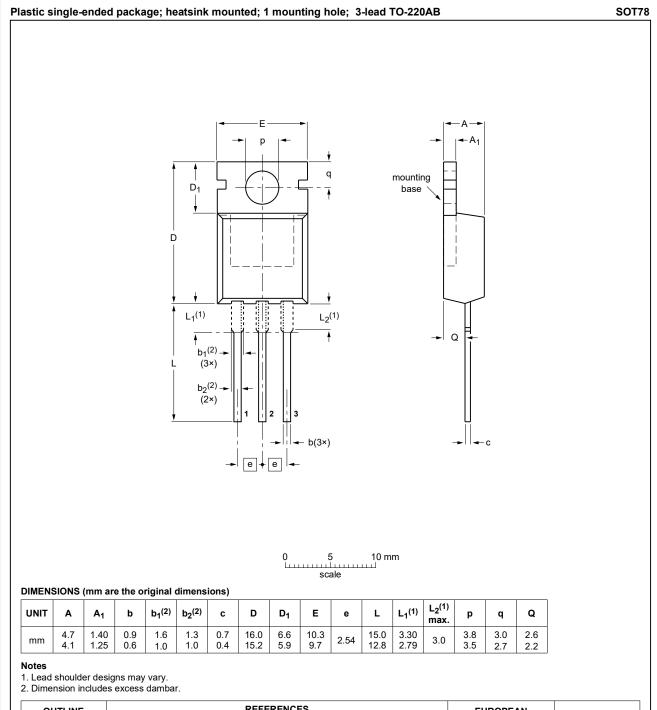


Fig. 12. Rate of change of commutating current as a function of junction temperature; minimum values

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## 10. Package outline



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13
				- 1	

Fig. 13. Package outline TO-220AB (SOT78)

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### 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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